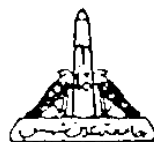


Ain Shams University
Faculty of Science
Physics Department



*Structural, Transport and Optical
Properties of In_2S_3 Thin Films*

Thesis
Submitted for the degree of Ph.D.
in
Physics

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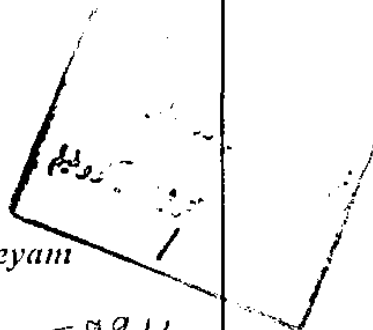
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
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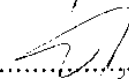
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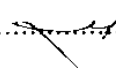
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Acknowldegment

ACKNOWLEDGMENT

The all thanks for **Allah**, the lord of all being.

The author wishes indebted with his utmost thanks to Professor Dr. *A.A.El-Shazly* and Professor Dr. *B.A. Khalifa* for continuous supervision, valuable suggestions and relevant recommendations in performing this work and interpreting the results.

Deepest gratitude to Dr. *H.S.Metwally* for his supervision.

The author wishes to thank Professor Dr. *M.M.El-Nahass*, Professor Dr. *A.El-Falaky* and Dr. *D.Abd El-Hady* for their valuable help and fruitful advice throughout this work.

The author wishes to express his sincere gratitude to Professor Dr. *M.F.El-Sharkawy*, Head of Physics Department Faculty of Science Ain Shams University, for his rendering facilities.

Finally the assistance of the *members* of the *Thin film laboratory* is highly appreciated.

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